

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously presented): A copper sulfate comprising a high purity copper sulfate having a purity of 99.99wt% or higher and contents of Ag impurities of less than 0.01wtppm, metalloid element impurities of As, Sb, and Bi of less than 0.1wtppm, respectively, radioactive elements of U and Th of less than 0.001wtppm, respectively, and heavy metal elements of Fe, Cr, and Ni of less than 0.1wtppm, respectively.

Claims 2-6 (canceled).

Claim 7 (previously presented): A method of manufacturing high purity copper sulfate comprising the steps of dissolving copper sulfate having a purity of 95 to 99.5 wt%, and subjecting this to active carbon treatment and solvent extraction to realize recrystallization and to produce a high purity copper sulfate having a purity of 99.99wt% or higher and contents of Ag impurities of less than 0.01wtppm, metalloid element impurities of As, Sb, and Bi of less than 0.1wtppm, respectively, radioactive elements of U and Th of less than 0.001wtppm, respectively, and heavy metal elements of Fe, Cr, and Ni of less than 0.1wtppm, respectively.

Claim 8 (canceled).

Claim 9 (currently amended): A copper sulfate according to claim 1, wherein organic and foreign matter impurities are contained at a level such that, when said copper sulfate is dissolved in water, undissolved residue of $1\mu\text{m}$ or greater ~~in water~~ exists in an amount of 100 residues/L or less.

Claim 10 (previously presented): A copper sulfate according to claim 9, wherein said high purity copper sulfate has a purity of 99.999wt% or higher.

Claim 11 (previously presented): A copper sulfate according to claim 1, wherein said high purity copper sulfate has a purity of 99.999wt% or higher.

Claim 12 (currently amended): A method according to claim 7, wherein organic and foreign matter impurities are reduced to a level such that, when said high purity copper sulfate is dissolved in water, undissolved residue of $1\mu\text{m}$ or greater ~~in water~~ exists in said high purity copper sulfate in an amount of 100 residues/L or less.

Claim 13 (previously presented): A method according to claim 12, wherein said high purity copper sulfate has a purity of 99.999wt% or higher.

Claim 14 (previously presented): A method according to claim 7, wherein said high purity copper sulfate has a purity of 99.999wt% or higher.

Claim 15 (new): A method of manufacturing high purity copper sulfate, comprising the steps of:

dissolving copper sulfate crystals or copper metal raw material having a purity of 95 to 99.9wt% in purified water or acid at room temperature to form a solution;

subjecting said solution to solvent extraction and active carbon treatment;

after said solvent extraction and active carbon treatment, filtering said solution, heating the filtrate to a temperature of 50 to 100°C, and performing evaporative concentration thereto;

after said filtering, heating and evaporative concentration, cooling said filtrate to room temperature to deposit high purity copper sulfate crystals of blue color having a purity of 99.99wt% or higher and contents of Ag impurities of less than 0.01wtppm, metalloid element impurities of As, Sb, and Bi of less than 0.1wtppm, respectively, radioactive elements of U and Th of less than 0.001wtppm, respectively, and heavy metal elements of Fe, Cr, and Ni of less than 0.1wtppm, respectively.

Claim 16 (new): A method according to claim 15, wherein during said dissolving step, the purified water or acid is diluted sulfuric acid.

Claim 17 (new): A method according to claim 16, wherein, during said dissolving step, the copper sulfate crystals or copper metal raw material is copper sulfate crystals ($\text{Cu}_2\text{SO}_4 \cdot 5\text{H}_2\text{O}$) having a purity of 95 to 99.9wt%.

Claim 18 (new): A method according to claim 15, wherein the solvent extraction is performed with D2EHPA.

Claim 19 (new): A method according to claim 15, wherein, during said cooling step, the depositing of high purity copper sulfate crystals is terminated such that a residual liquid containing non-recrystallized copper sulfate remains.

Claim 20 (new): A method according to claim 19, wherein the residual liquid is 2 to 40wt% of an original fluid volume of the filtrate.

Claim 21 (new): A method according to claim 19, further comprising the steps of removing the high purity copper sulfate crystals from the residual liquid and drying the high purity copper sulfate crystals at a drying temperature of 40 to 100°C.